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Secondary phases in Cu₂ZnSnS₄ films obtained by spray pyrolysis at different substrate

temperatures and Cu contents

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Abstract. Cu₂ZnSnS₄ (CZTS) thin films prepared by the spray pyrolysis method were studied. This

deposition method does not require sophisticated technological setup and allows to easily varying

different technological parameters, which is perspective in terms of mass application. Here we show how

the variation of the substrate temperature and of the Cu/Zn stoichiometry ratio in the precursor solutions

influence the optical and structural properties of CZTS film. The Raman spectra reveal that an increase in

the substrate temperature and Cu content leads to a higher disorder of the crystal structure and to the

secondary phase formation, in particular, Cu_{2-x}S. In turn, the formation of secondary phases significantly

affected the CZTS bandgap. We have found that the films with the substrate temperature 289°C and the

Cu/Zn stoichiometric ratio equal to 2.0 comprise a minimum content of secondary phases and having the

best crystal structure.

1

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